

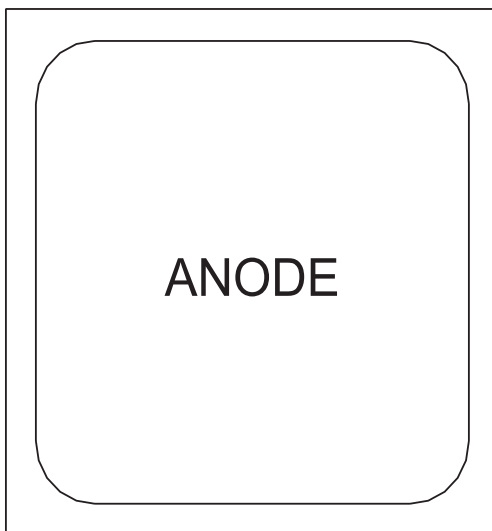
**PROCESS CPD24**  
**Fast Recovery Rectifier**  
1.0 Amp Glass Passivated Rectifier Chip

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	50 x 50 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

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**GROSS DIE PER 4 INCH WAFER**

4,520

**PRINCIPAL DEVICE TYPES**

1N4933 thru 1N4937  
1N4942 thru 1N4948  
1N5615 thru 1N5623  
CMR1F-02M Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data  
for this Chip Process,  
please visit our website at:

[www.centalsemi.com/chip](http://www.centalsemi.com/chip)

R1 (1-August 2002)